TrenchMOS™ transistor Logic level FET

BUK92150-55A

GENERAL DESCRIPTION

N-channel enhancement mode logic level field-effect power transistor in a plastic envelope suitable for surface mounting. Using '**trench**' technology the device features very low on-state resistance. It is intended for use in automotive and general purpose switching applications.

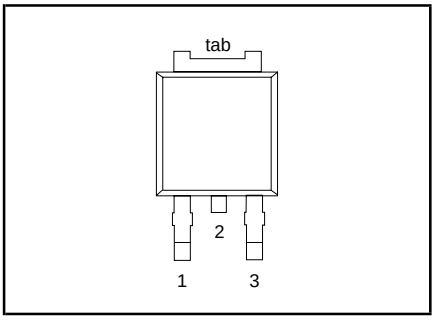
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	Drain-source voltage	55	V
I_D	Drain current (DC)	10.7	A
P_{tot}	Total power dissipation	36	W
T_j	Junction temperature	175	˚C
$R_{DS(ON)}$	Drain-source on-state resistance V_{GS} = 5 V	150	mΩ
	V_{GS} = 10 V	137	mΩ

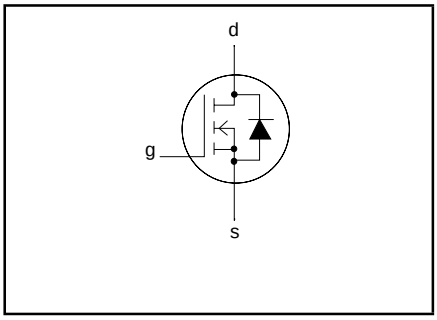
PINNING - SOT428

PIN	DESCRIPTION
1	gate
2	drain
3	source
tab	drain

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Drain-source voltage	-	-	55	V
V_{DGR}	Drain-gate voltage	R_{GS} = 20 kΩ	-	55	V
$\pm V_{GS}$	Gate-source voltage	-	-	10	V
$\pm V_{GSM}$	Non-repetitive gate-source voltage	$t_p \leq 50\mu S$	-	15	V
I_D	Drain current (DC)	T_{mb} = 25 ˚C	-	10.7	A
I_D	Drain current (DC)	T_{mb} = 100 ˚C	-	7.5	A
I_{DM}	Drain current (pulse peak value)	T_{mb} = 25 ˚C	-	43	A
P_{tot}	Total power dissipation	T_{mb} = 25 ˚C	-	36	W
T_{stg}, T_j	Storage & operating temperature	-	- 55	175	˚C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base	-	-	4.1	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	Minimum footprint, FR4 board	71.4	-	K/W

STATIC CHARACTERISTICS

T_j= 25˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V; I_D = 0.25 mA;	55	-	-	V
		T_j = -55˚C	50	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	V_{DS} = V_{GS}; I_D = 1 mA	1	1.5	2.0	V
		T_j = 175˚C	0.5	-	-	V
		T_j = -55˚C	-	-	2.3	V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 55 V; V_{GS} = 0 V;	-	0.05	10	µA
		T_j = 175˚C	-	-	500	µA
I_{GSS}	Gate source leakage current	V_{GS} = ±10 V; V_{DS} = 0 V	-	2	100	nA
$R_{DS(ON)}$	Drain-source on-state resistance	V_{GS} = 5 V; I_D = 5 A	-	128	150	mΩ
		T_j = 175˚C	-	-	315	mΩ
		V_{GS} = 10 V; I_D = 5 A	-	116	137	mΩ
		V_{GS} = 4.5 V; I_D = 5 A	-	-	161	mΩ

DYNAMIC CHARACTERISTICS1

T_{mb} = 25˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C_{iss}	Input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz	-	250	339	pF
C_{oss}	Output capacitance		-	54	65	pF
C_{rss}	Feedback capacitance		-	42	58	pF
$t_{d\ on}$	Turn-on delay time	V_{DD} = 30 V; R_{load} =2.7Ω;	-	6	16	ns
t_r	Turn-on rise time	V_{GS} = 5 V; R_G = 10 Ω	-	64	80	ns
$t_{d\ off}$	Turn-off delay time		-	20	30	ns
t_f	Turn-off fall time		-	26	40	ns
L_d	Internal drain inductance	Measured from upper edge of drain tab to centre of die	-	2.5	-	nH
L_s	Internal source inductance	Measured from source lead soldering point to source bond pad	-	7.5	-	nH

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

T_j = 25˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current		-	-	10.7	A
I_{DRM}	Pulsed reverse drain current		-	-	43	A
V_{SD}	Diode forward voltage	I_F = 5 A; V_{GS} = 0 V	-	0.85	1.2	V
		I_F = 10.7 A; V_{GS} = 0 V	-	1.1	-	V
t_{rr}	Reverse recovery time	I_F = 13 A; -dI_F/dt = 100 A/µs;	-	24	-	ns
Q_{rr}	Reverse recovery charge	V_{GS} = -10 V; V_R = 30 V	-	0.026	-	µC

AVALANCHE LIMITING VALUE

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
W_{DSS}	Drain-source non-repetitive unclamped inductive turn-off energy	I_D = 8 A; V_{DD} ≤ 25 V; V_{GS} = 5 V; R_{GS} = 50 Ω; T_{mb} = 25 ˚C	-	-	25	mJ

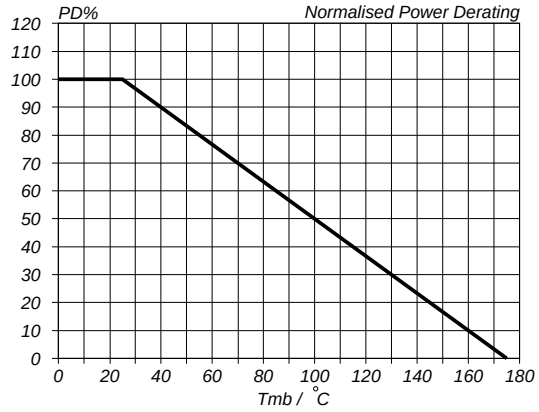


Fig.1. Normalised power dissipation.
PD% = 100·P_D/$P_{D\ 25\ °C}$ = f(T_{mb})

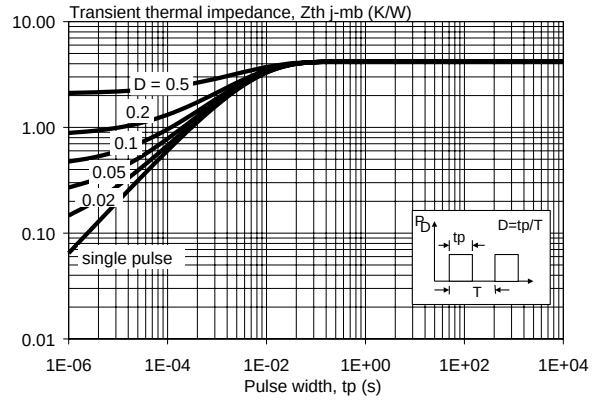


Fig.4. Transient thermal impedance.
$Z_{th\ j\text{-}mb}$ = f(t); parameter D = t_p/T

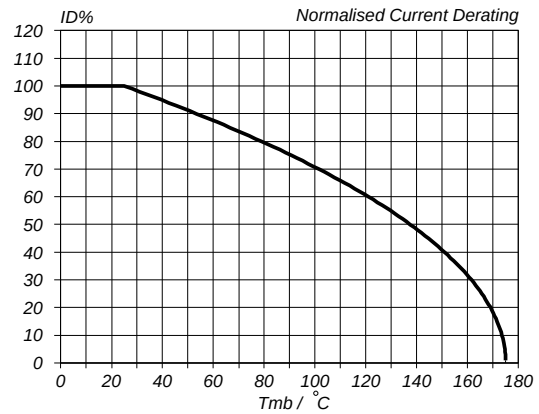


Fig.2. Normalised continuous drain current.
ID% = 100·I_D/$I_{D\ 25\ °C}$ = f(T_{mb}); conditions: V_{GS} ≥ 5 V

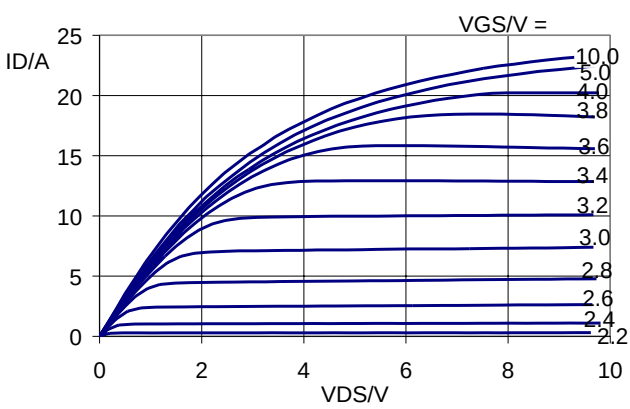


Fig.5. Typical output characteristics, T_j = 25 ˚C.
I_D = f(V_{DS}); parameter V_{GS}

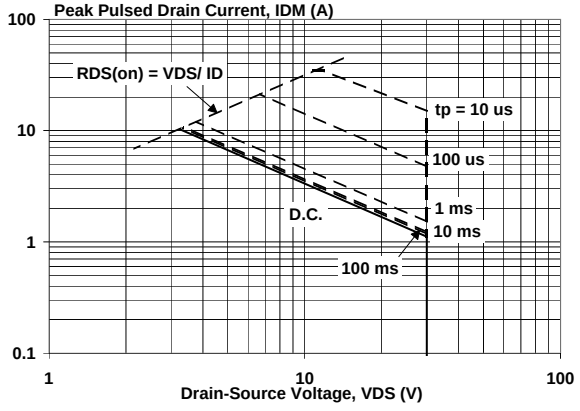


Fig.3. Safe operating area. T_{mb} = 25 ˚C
I_D & I_{DM} = f(V_{DS}); I_{DM} single pulse; parameter t_p

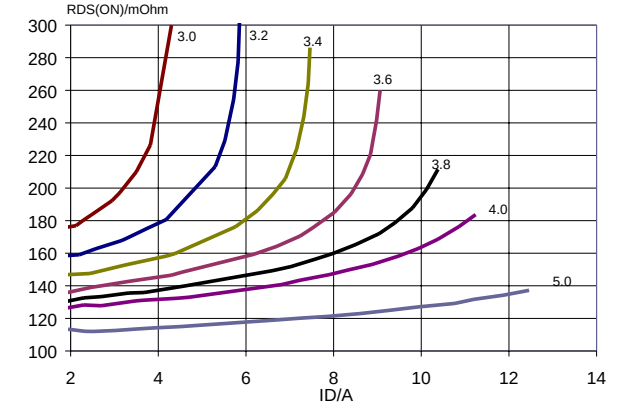


Fig.6. Typical on-state resistance, T_j = 25 ˚C.
$R_{DS(ON)}$ = f(I_D); parameter V_{GS}

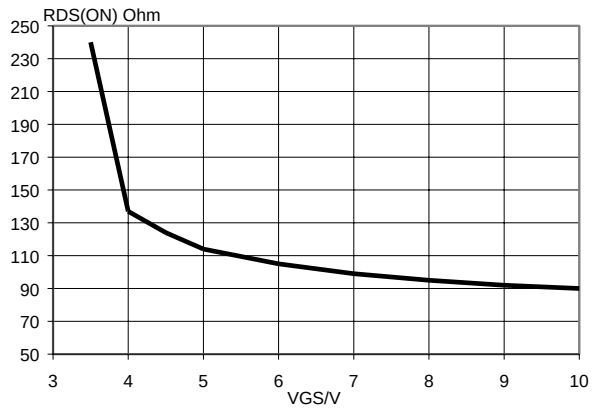


Fig.7. Typical on-state resistance, T_j = 25 ˚C. $R_{DS(ON)} = f(V_{GS})$; conditions: I_D = 13 A;

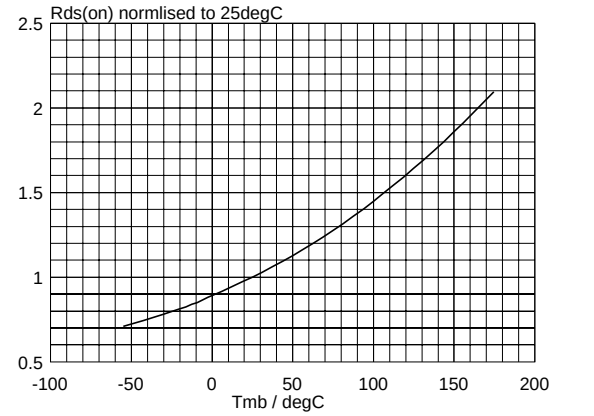


Fig.10. Normalised drain-source on-state resistance. $a = R_{DS(ON)}/R_{DS(ON)25\,^{\circ}C} = f(T_j)$; I_D = 25 A; V_{GS} = 5 V

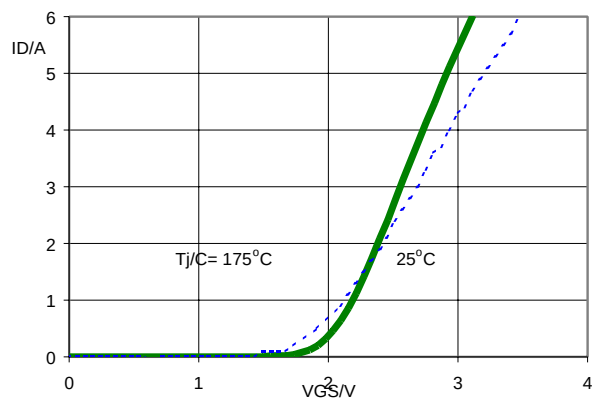


Fig.8. Typical transfer characteristics. $I_D = f(V_{GS})$; conditions: V_{DS} = 25 V; parameter T_j

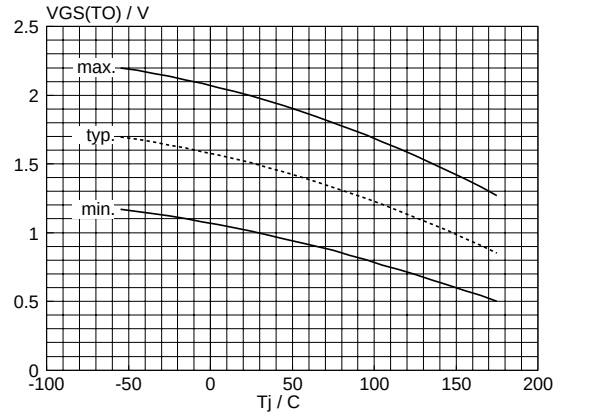


Fig.11. Gate threshold voltage. $V_{GS(TO)} = f(T_j)$; conditions: I_D = 1 mA; $V_{DS} = V_{GS}$

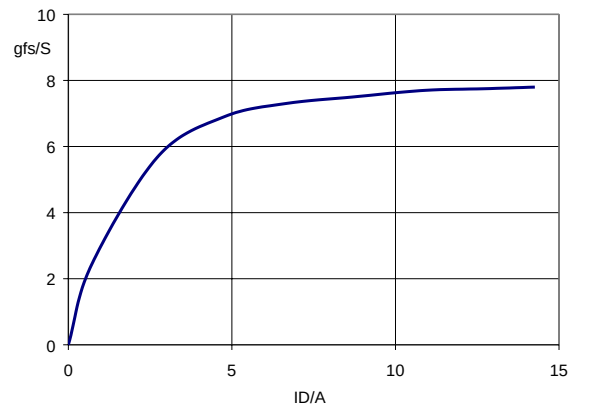


Fig.9. Typical transconductance, T_j = 25 ˚C. $g_{fs} = f(I_D)$; conditions: V_{DS} = 25 V

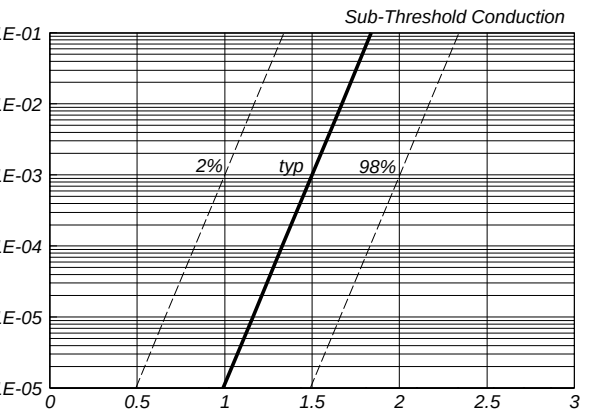


Fig.12. Sub-threshold drain current. $I_D = f(V_{GS})$; conditions: T_j = 25 ˚C; $V_{DS} = V_{GS}$

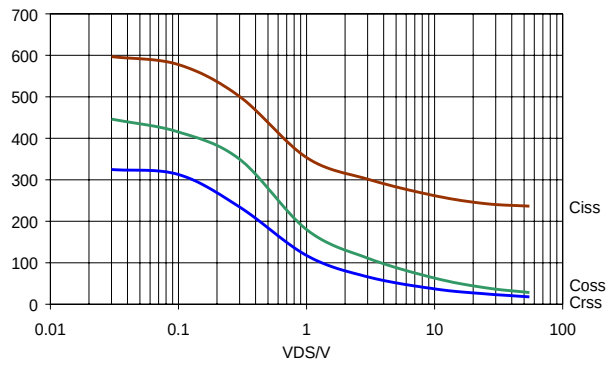


Fig.13. Typical capacitances, C_{iss}, C_{oss}, C_{rss}. C = f(V_{DS}); conditions: V_{GS} = 0 V; f = 1 MHz

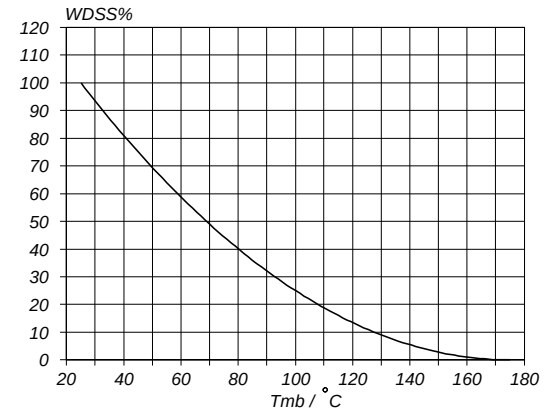


Fig.16. Normalised avalanche energy rating. W_{DSS}% = f(T_{mb}); conditions: I_D = 75 A

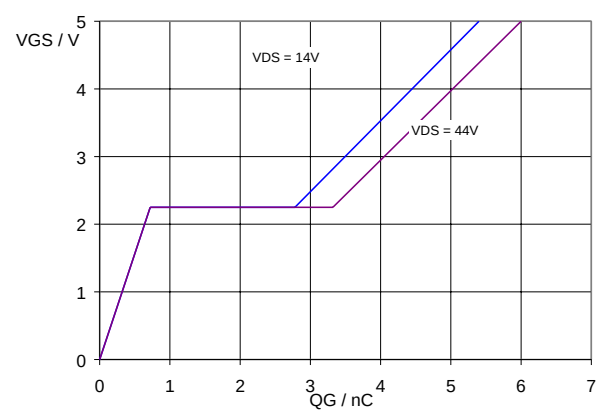


Fig.14. Typical turn-on gate-charge characteristics. V_{GS} = f(Q_G); conditions: I_D = 3 A; parameter V_{DS}

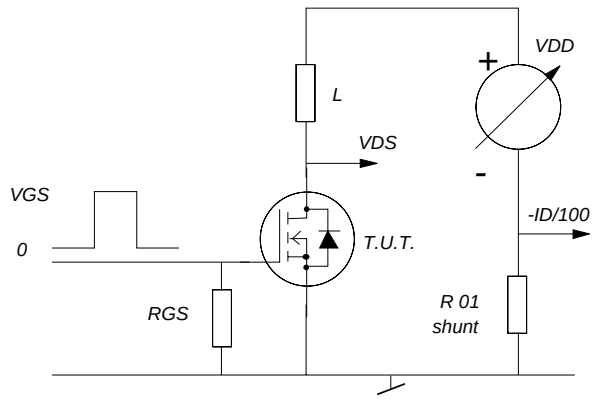


Fig.17. Avalanche energy test circuit.

$$W_{DSS} = 0.5 \cdot L I_D^2 \cdot BV_{DSS}/(BV_{DSS} - V_{DD})$$

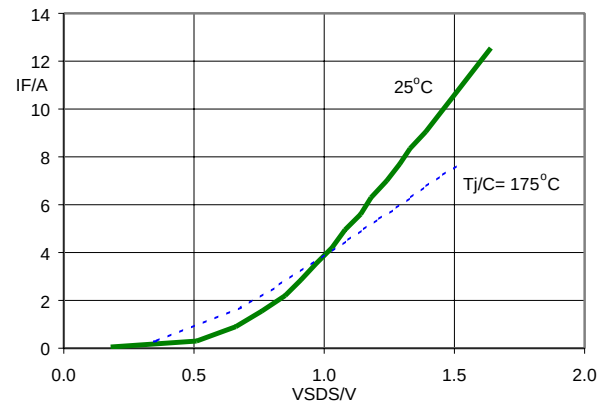


Fig.15. Typical reverse diode current. I_F = f(V_{SDS}); conditions: V_{GS} = 0 V; parameter T_j

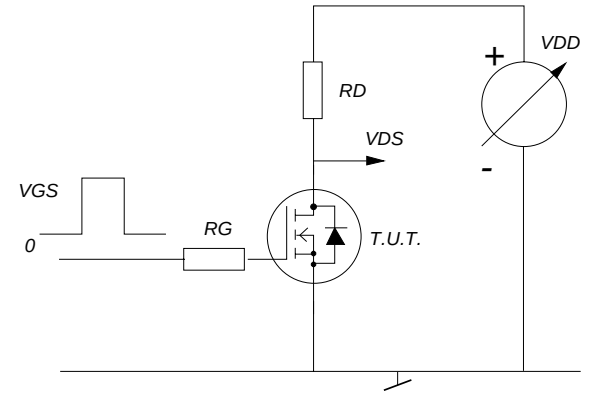
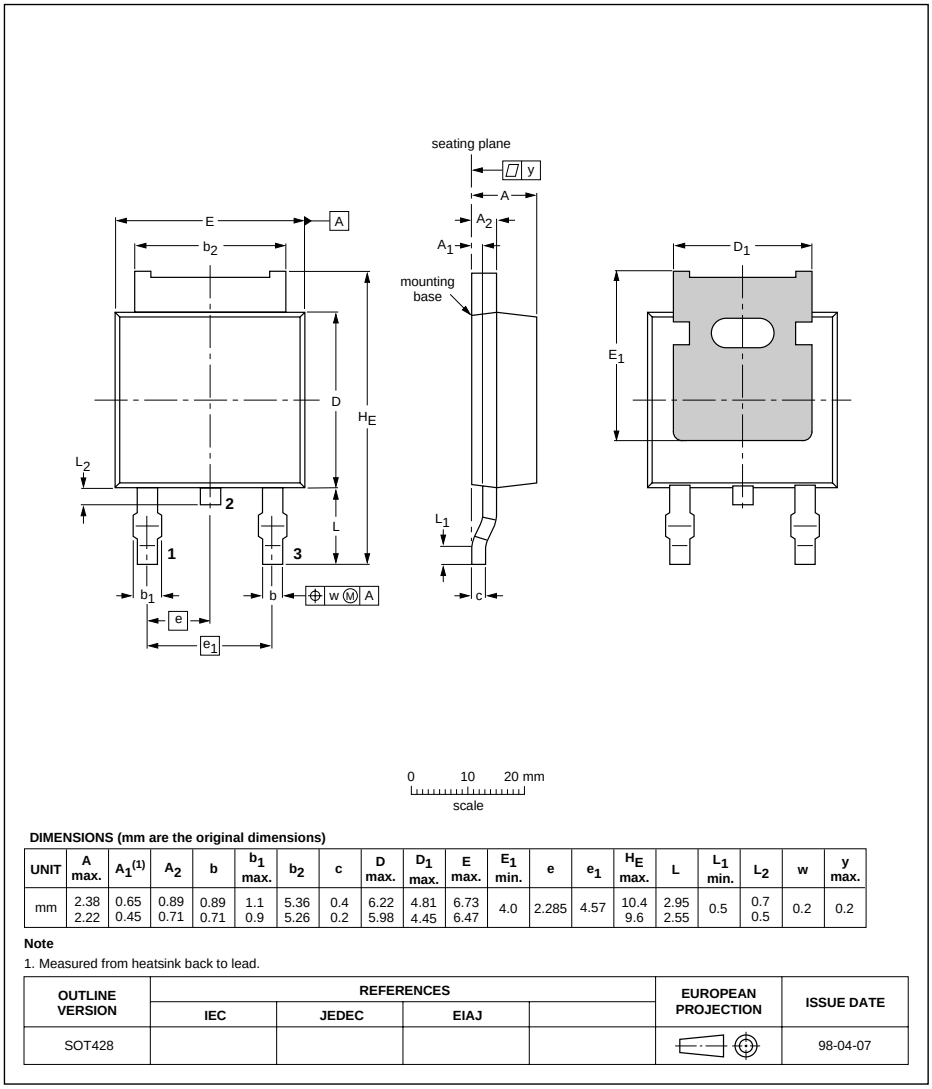


Fig.18. Switching test circuit.

MECHANICAL DATA

Plastic single-ended surface mounted package (Philips version of D-PAK); 3 leads (one lead cropped) **SOT428**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1 (1)	A_2	b	b_1 max.	b_2	c	D max.	D_1 max.	E max.	E_1 min.	e	e_1	H_E max.	L	L_1 min.	L_2	w	y max.
mm	2.38 2.22	0.65 0.45	0.89 0.71	0.89 0.71	1.1 0.9	5.36 5.26	0.4 0.2	6.22 5.98	4.81 4.45	6.73 6.47	4.0	2.285	4.57	10.4 9.6	2.95 2.55	0.5	0.7 0.5	0.2	0.2

Note

1. Measured from heatsink back to lead.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT428						98-04-07

Fig.19. SOT428 surface mounting package. Centre pin connected to mounting base.

Notes

1. This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.
2. Refer to SMD Footprint Design and Soldering Guidelines, Data Handbook SC18.
3. Epoxy meets UL94 V0 at 1/8".

MOUNTING INSTRUCTIONS

Dimensions in mm

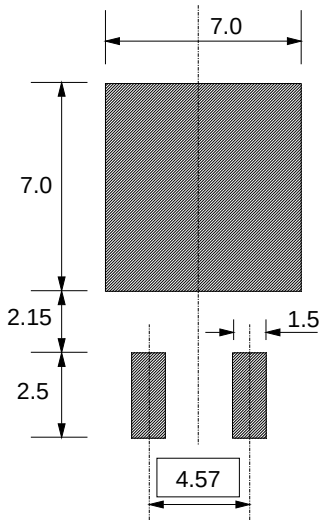


Fig.20. SOT428 : soldering pattern for surface mounting.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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